TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

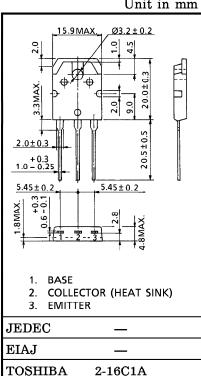
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POWER AMPLIFIER APPLICATIONS

- Complementary to 2SC5358
- Recommend for 80W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	-230	V
Collector-Emitter Voltage	VCEO	-230	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	IC	-15	A
Base Current	IB	-1.5	A
Collector Power Dissipation (Tc=25°C)	PC	150	w
Junction Temperature	Tj	150	°C
Storage Temperature Range	T_{stg}	$-55 \sim 150$	°C



Weight: 4.7g (Typ.)

CHARACTERISTIC SYMBOL TEST CONDITION MIN. TYP. MAX. UNIT Collector Cut-off Current $V_{CB} = -230V, I_E = 0$ -5.0**ICBO** μA Emitter Cut-off Current $V_{EB} = -5V, I_C = 0$ -5.0**I**EBO μA Collector-Emitter v V (BR) CEO $I_{C} = -50 m A$, $I_{B} = 0$ -230Breakdown Voltage $h_{FE}(1)$ $V_{CE} = -5V, I_C = -1A$ 55 160 DC Current Gain (Note) $V_{CE} = -5V, I_{C} = -7A$ 35 70 $h_{FE}(2)$ Collector-Emitter VCE (sat) $I_{C} = -8A$, $I_{B} = -0.8A$ -1.5-3.0v Saturation Voltage **Base-Emitter Voltage** $V_{CE} = -5V, I_{C} = -7A$ -1.0v VBE -1.5 $V_{CE} = -5V, I_C = -1A$ Transition Frequency 30 MHz fŢ Collector Output Capacitance Cob $V_{CB} = -10V, I_E = 0, f = 1MHz$ 360 pF

ELECTRICAL CHARACTERISTICS ($Ta = 25^{\circ}C$)

(Note) $h_{FE(1)}$ Classification R : 55~110, O : 80~160

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Unit in mm

